

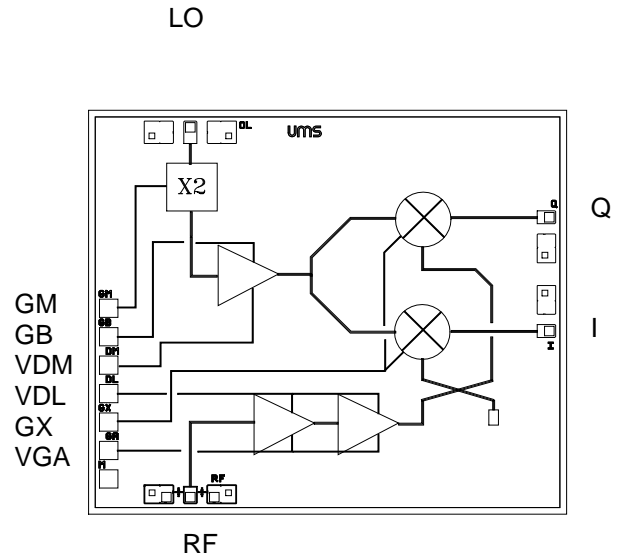
36-40GHz Integrated Down Converter

GaAs Monolithic Microwave IC

Description

The CHR2296 is a multifunction chip which integrates a LO time two multiplier, a balanced cold FET mixer, and a RF LNA. It is designed for a wide range of applications, typically commercial communication systems. The backside of the chip is both RF and DC grounds. This helps simplify the assembly process.

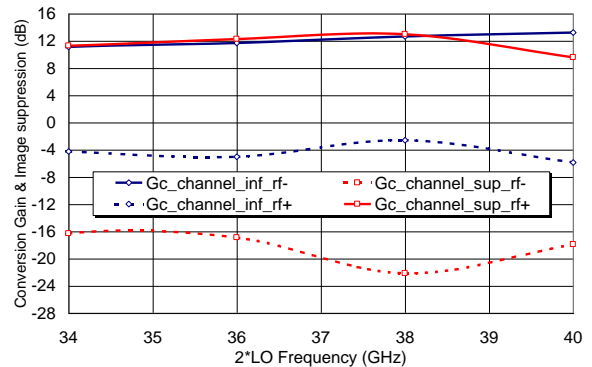
The circuit is manufactured with a pHEMT process, 0.25µm gate length, via holes through the substrate, air bridges and electron beam gate lithography. It is available in chip form.



Main Features

- Broadband performances: 36-40GHz
- 11 dB conversion gain
- 5dB noise figure, for IF>0.1GHz
- 10dBm LO input power
- -10dBm RF input power (1dB gain comp.)
- Low DC power consumption, 110mA@3.5V
- Chip size: 2.49 X 1.97 X 0.10mm

Typical on wafer measurement:
Conversion Gain & Image suppression
@ IF=1GHz



Main Characteristics

Tamb. = 25°C

Symbol	Parameter	Min	Typ	Max	Unit
F _{RF}	RF frequency range	36		40	GHz
F _{LO}	LO frequency range	17		20	GHz
F _{IF}	IF frequency range	DC		1.5	GHz
G _c	Conversion gain	9	11		dB

ESD Protection: Electrostatic discharge sensitive device. Observe handling precautions!

Electrical Characteristics for Broadband Operation

Tamb = +25°C, Vd = 3.5V

Symbol	Parameter	Min	Typ	Max	Unit
F _{RF}	RF frequency range	36		40	GHz
F _{LO}	LO frequency range	17		20	GHz
F _{IF}	IF frequency range	DC		1.5	GHz
G _c	Conversion gain ⁽¹⁾	9	11		dB
NF	Noise Figure, for IF>0.1GHz ⁽¹⁾		5		dB
P _{LO}	LO Input power		+10		dBm
Img Sup	Image Suppression	13	15		dBc
P1dB	Input power at 1dB gain compression		-10		dBm
LO VSWR	Input LO VSWR ⁽¹⁾		2.0:1		
RF VSWR	Input RF VSWR ⁽¹⁾		3.0:1		
I _d	Bias current ⁽²⁾		110		mA

(1) On Wafer measurements

(2) Current source biasing network is recommended. Optimum performances for I_{dm} = 50mA and I_{dl} = 60mA

Absolute Maximum Ratings

Tamb. = 25°C (1)

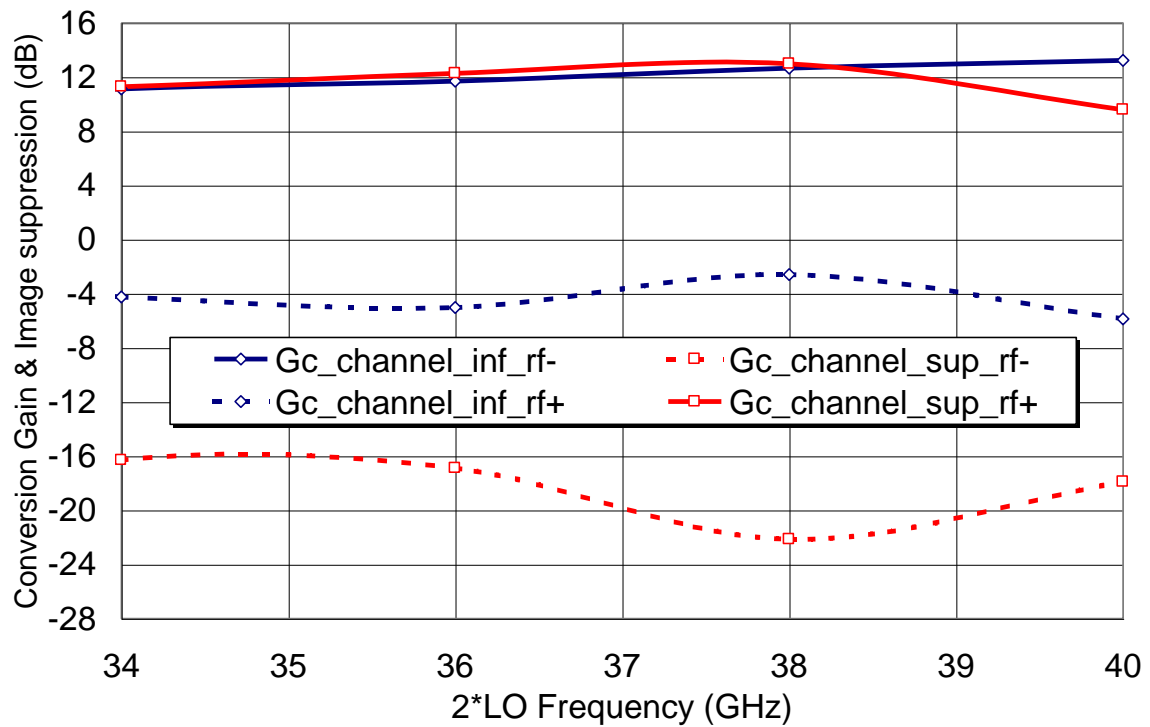
Symbol	Parameter	Values	Unit
V _d	Maximum drain bias voltage	4.0	V
I _d	Maximum drain bias current	200	mA
V _g	Gate bias voltage	-2.0 to +0.4	V
V _{gd}	Minimum negative gate drain voltage (V _g – V _d)	-5	V
P _{in}	Maximum peak input power overdrive (2)	+15	dBm
T _{ch}	Maximum channel temperature	175	°C
T _a	Operating temperature range	-40 to +85	°C
T _{stg}	Storage temperature range	-55 to +125	°C

(1) Operation of this device above anyone of these parameters may cause permanent damage.

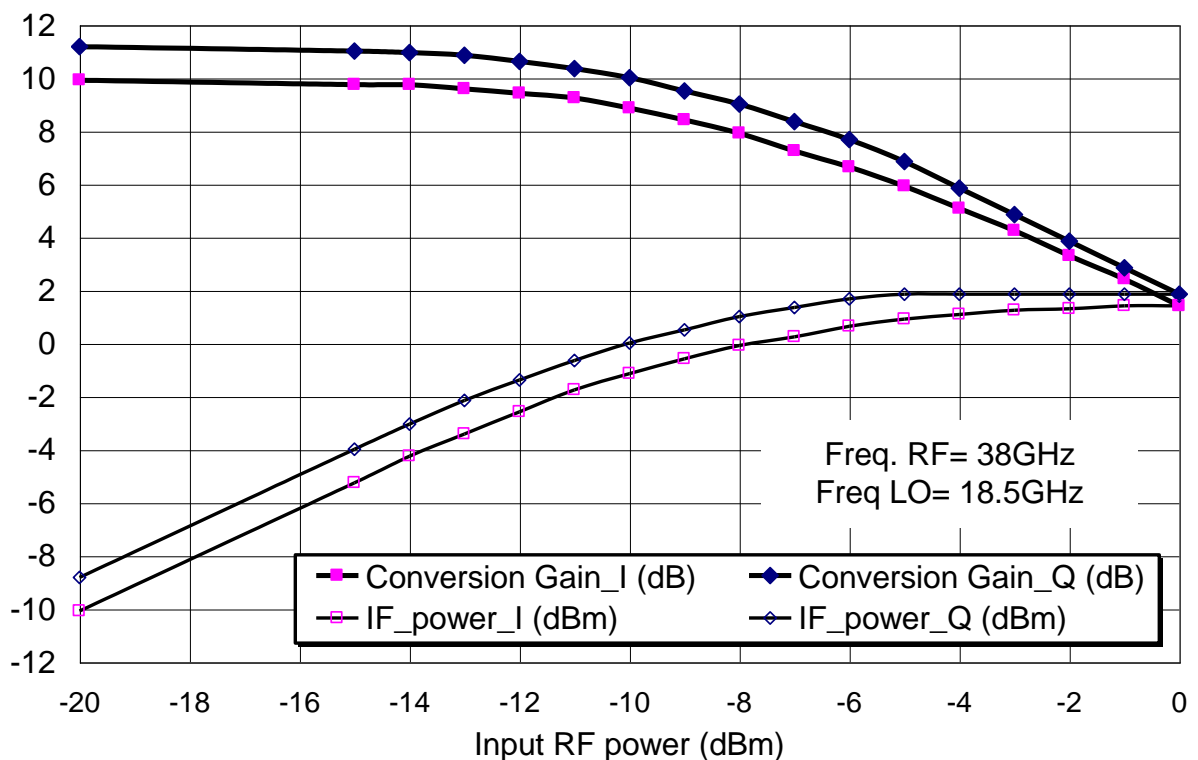
(2) Duration < 1s.

Typical On-wafer Measurements

Bias Conditions : $V_{dm}= V_{dl}= 3.5 V$, $V_{gm}= -0.9V$, $V_{gb}= -0.4V$, $V_{gx}= -0.8V$, $V_{ga}= -0.5V$



Conversion gain & Image suppression with a 90° IQ combiner @ IF=1GHz



Input RF compression by channel

Notes

